BSO4804 Datasheet

DiGi Electronics Part Number	BSO4804-DG
Manufacturer	Infineon Technologies
Manufacturer Product Number	BSO4804
Description	MOSFET 2N-CH 30V 8A 8DSO
Detailed Description	Mosfet Array 30V 8A 2W Surface Mount PG-DSO-8

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BSO4804	Infineon Technologies
Series:	Product Status:
OptiMOS™	Obsolete
Technology:	Configuration:
MOSFET (Metal Oxide)	2 N-Channel (Dual)
FET Feature:	Drain to Source Voltage (Vdss):
Logic Level Gate	30V
Current - Continuous Drain (Id) @ 25°C:	Rds On (Max) @ Id, Vgs:
8A	20mOhm @ 8A, 10V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
2V @ 30µA	17nC @ 5V
Input Capacitance (Ciss) (Max) @ Vds:	Power - Max:
870pF @ 25V	2W
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
8-SOIC (0.154", 3.90mm Width)	PG-DSO-8
Base Product Number:	
BSO4804	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0095

BSO4804

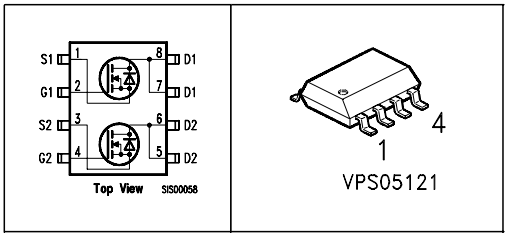
OptiMOS® Small-Signal-Transistor

Feature

- N-Channel
- Enhancement mode
- Logic Level
- Excellent Gate Charge x $R_{DS(on)}$ product (FOM)
- 150°C operating temperature
- Avalanche rated
- d*v*/d*t* rated
- Ideal for fast switching applications
- Pb-free lead plating; RoHS compliant

Product Summary

V_{DS}	30	V
$R_{DS(on)}$	20	mΩ
I_D	8	A



Type	Package	Ordering Code	Marking
BSO4804	PG-DSO-8-7	Q67042-S4097	4804

Maximum Ratings,at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D		A
T_A=25°C		8	
T_A=70°C		6.4	
Pulsed drain current	$I_{D\ puls}$	32	
T_A=25°C			
Avalanche energy, single pulse	E_{AS}	90	mJ
I_D=8 A , V_{DD}=25V, R_{GS}=25Ω			
Reverse diode d*v*/d*t*	d*v*/d*t*	6	kV/µs
I_S=8A, V_{DS}=24V, d*i*/d*t*=200A/µs, T_{jmax}=150°C			
Gate source voltage	V_{GS}	±20	V
Power dissipation	P_{tot}	2	W
T_A=25°C			
Operating and storage temperature	T_j , T_{stg}	-55... +150	°C
IEC climatic category; DIN IEC 68-1		55/150/56	

Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - soldering point	R_{thJS}	-	-	45	K/W
SMD version, device on PCB:	R_{thJA}				
@ min. footprint; t ≤ 10 sec.		-	-	110	
@ 6 cm^2 cooling area [1]; t ≤ 10 sec.		-	-	62.5	

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain-source breakdown voltage V_{GS}=0V, I_D=1mA	$V_{(BR)DSS}$	30	-	-	V
Gate threshold voltage, V_{GS} = V_{DS} I_D=30µA	$V_{GS(th)}$	1.2	1.6	2	
Zero gate voltage drain current	I_{DSS}				µA
V_{DS}=30V, V_{GS}=0V, T_j=25°C		-	0.01	1	
V_{DS}=30V, V_{GS}=0V, T_j=125°C		-	10	100	
Gate-source leakage current V_{GS}=20V, V_{DS}=0V	I_{GSS}	-	1	100	nA
Drain-source on-state resistance V_{GS}=4.5V, I_D=6.7A	$R_{DS(on)}$	-	23.8	28.2	mΩ
Drain-source on-state resistance V_{GS}=10V, I_D=8A	$R_{DS(on)}$	-	17.4	20	

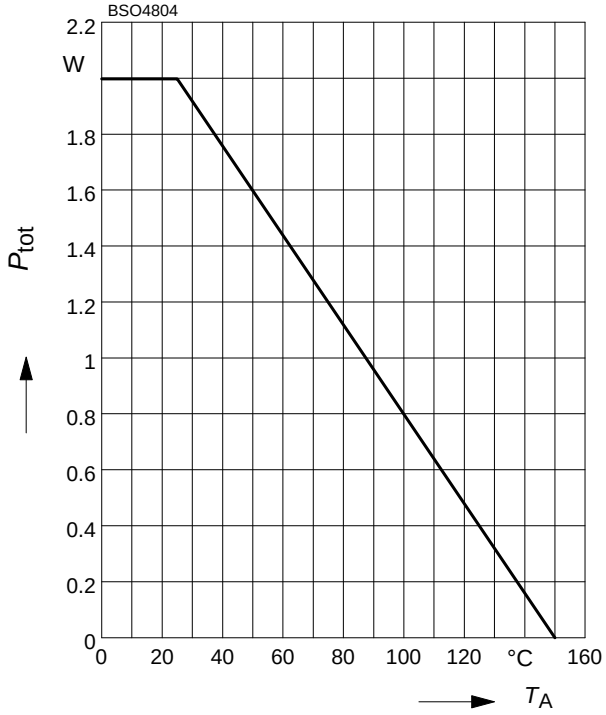
[1] Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic Characteristics						
Transconductance	g_{fs}	$V_{DS}\geq 2*I_D*R_{DS(on)max}$, I_D=6.4A	8.5	17	-	S
Input capacitance	C_{iss}	V_{GS}=0V, V_{DS}=25V, f=1MHz	-	700	870	pF
Output capacitance	C_{oss}		-	300	370	
Reverse transfer capacitance	C_{rss}		-	74	110	
Gate resistance	R_G		-	1.1	-	Ω
Turn-on delay time	$t_{d(on)}$	V_{DD}=15V, V_{GS}=4.5V, I_D=6.7A, R_G=9.1Ω	-	9.1	14	ns
Rise time	t_r		-	27	40	
Turn-off delay time	$t_{d(off)}$		-	18	27	
Fall time	t_f		-	24	36	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	V_{DD}=15V, I_D=8A	-	1.9	2.4	nC
Gate to drain charge	Q_{gd}		-	5.8	8.7	
Gate charge total	Q_g	V_{DD}=15V, I_D=8A, V_{GS}=0 to 5V	-	13.5	17	
Output charge	Q_{oss}	V_{DS}=15V, I_D=8A, V_{GS}=0V	-	10.3	13	
Gate plateau voltage	$V_{(plateau)}$	V_{DD}=15V, I_D=8A	-	2.8	-	V
Reverse Diode						
Inverse diode continuous forward current	I_S	T_A=25°C	-	-	1.8	A
Inverse diode direct current, pulsed	I_{SM}		-	-	32	
Inverse diode forward voltage	V_{SD}	V_{GS}=0V, I_F=1.8A	-	0.9	1.3	V
Reverse recovery time	t_{rr}	V_R=15V, I_F=I_S, di_F/dt=100A/µs	-	24	30	ns
Reverse recovery charge	Q_{rr}		-	16	20	nC

1 Power dissipation

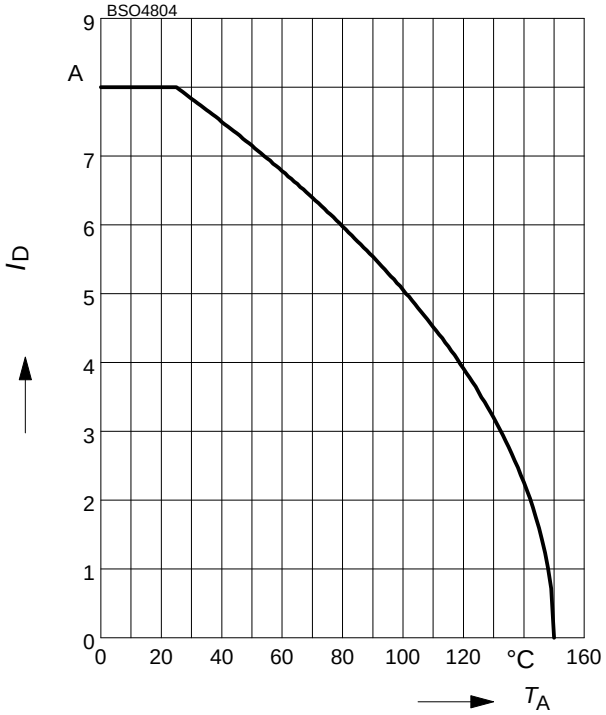
$P_{tot} = f(T_A)$



2 Drain current

$I_D = f(T_A)$

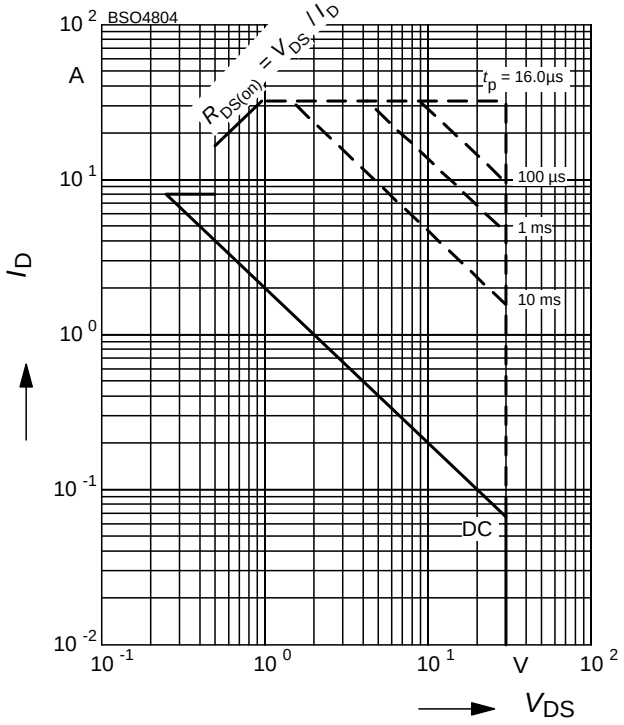
parameter: $V_{GS} \geq 10$ V



3 Safe operating area

$I_D = f(V_{DS})$

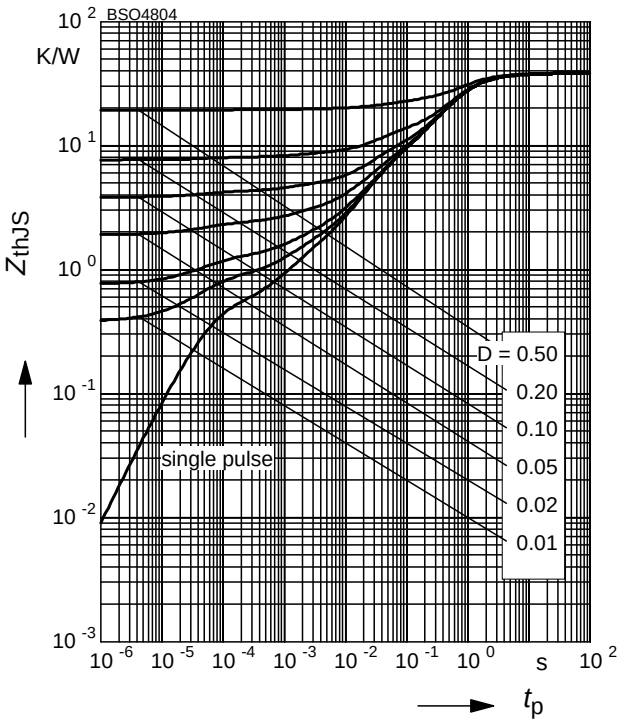
parameter : $D = 0$, $T_A = 25$ °C



4 Transient thermal impedance

$Z_{thJS} = f(t_p)$

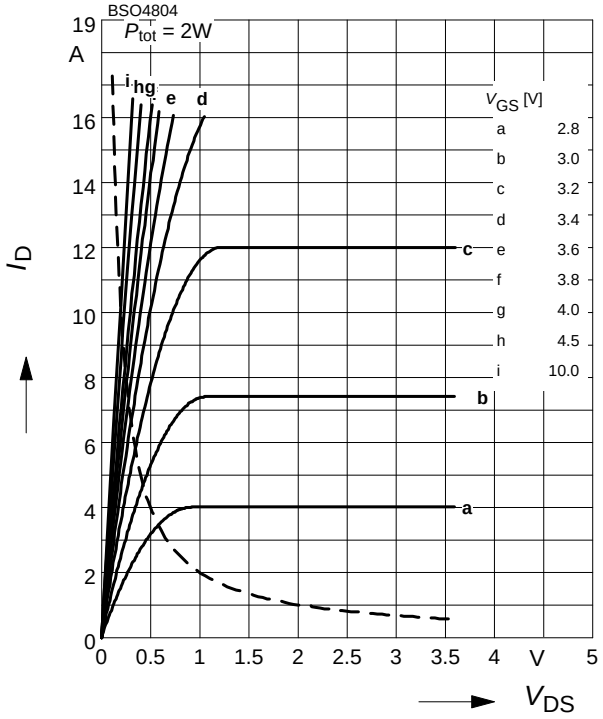
parameter : $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS})$; T_j=25°C

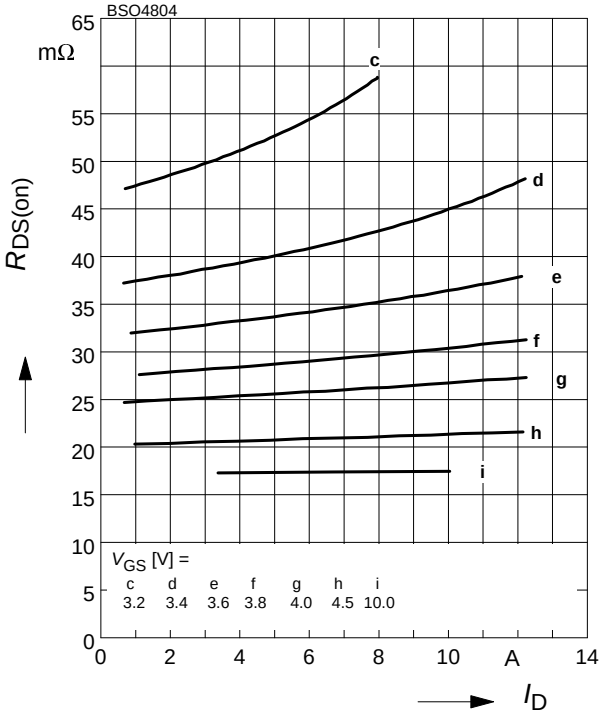
parameter: t_p = 80 µs



6 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

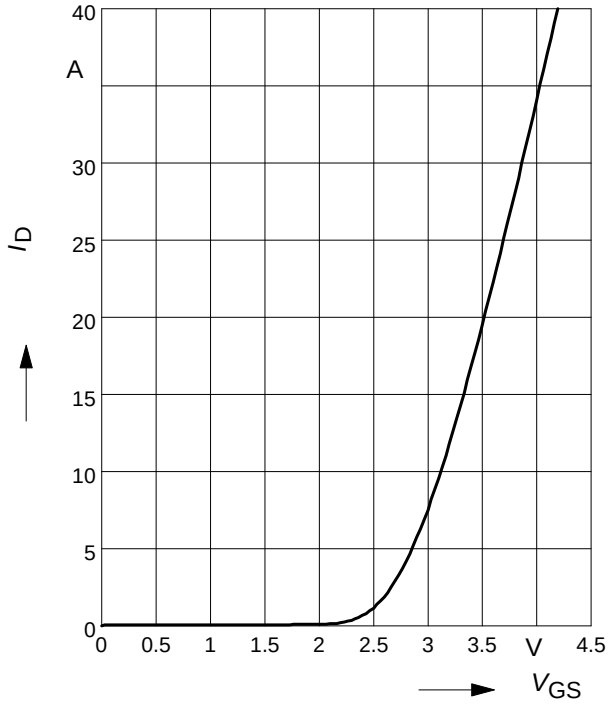
parameter: V_{GS}



7 Typ. transfer characteristics

$I_D = f(V_{GS})$; $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

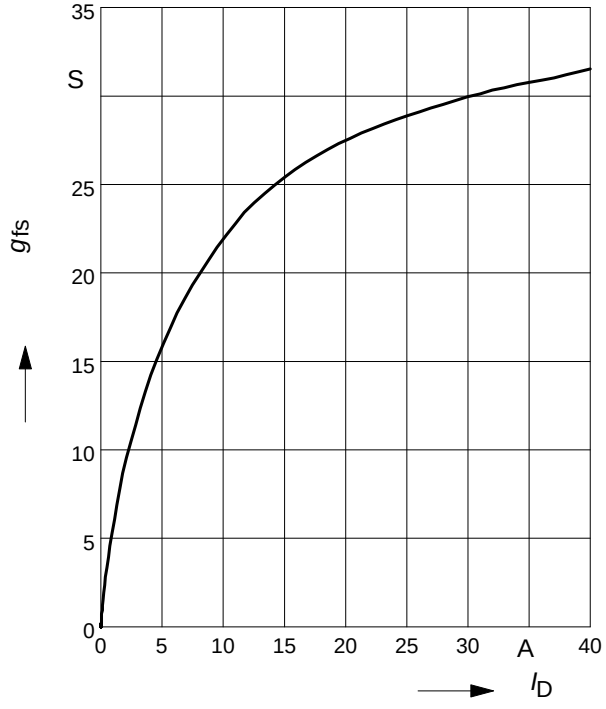
parameter: t_p = 80 µs



8 Typ. forward transconductance

g_{fs} = f(I_D); T_j=25°C

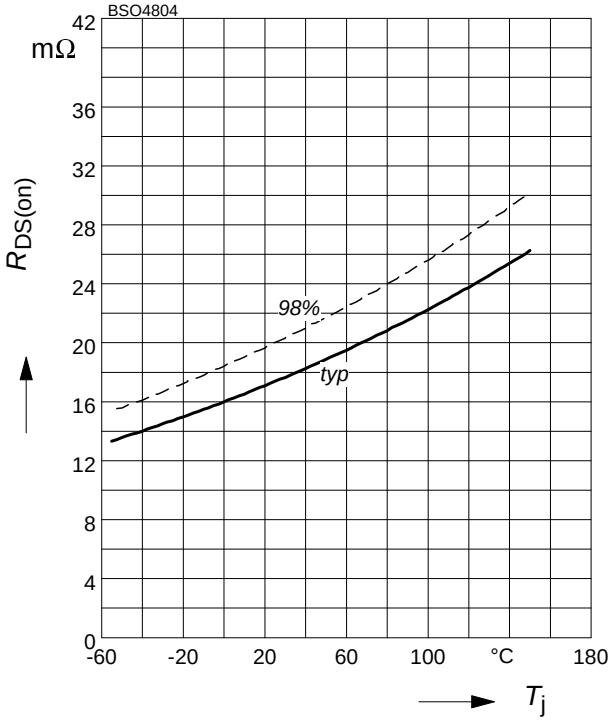
parameter: g_{fs}



9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j)$

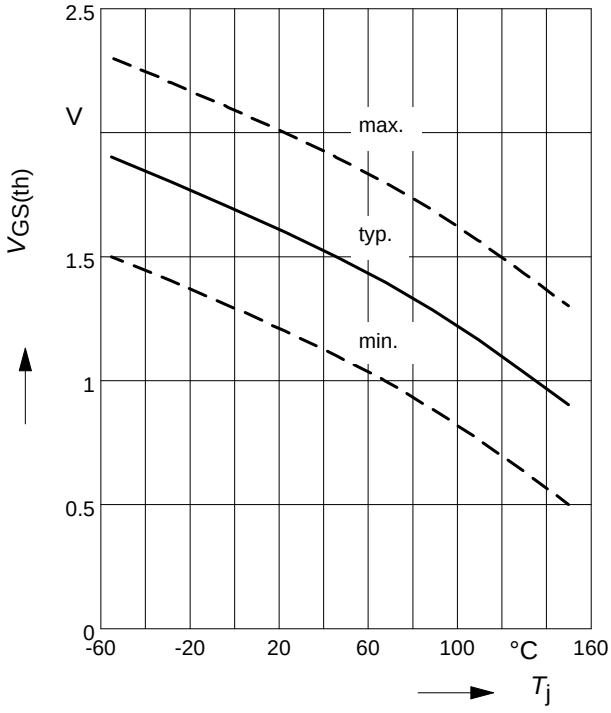
parameter : I_D = 8 A, V_{GS} = 10 V



10 Gate threshold voltage

$V_{GS(th)} = f(T_j)$

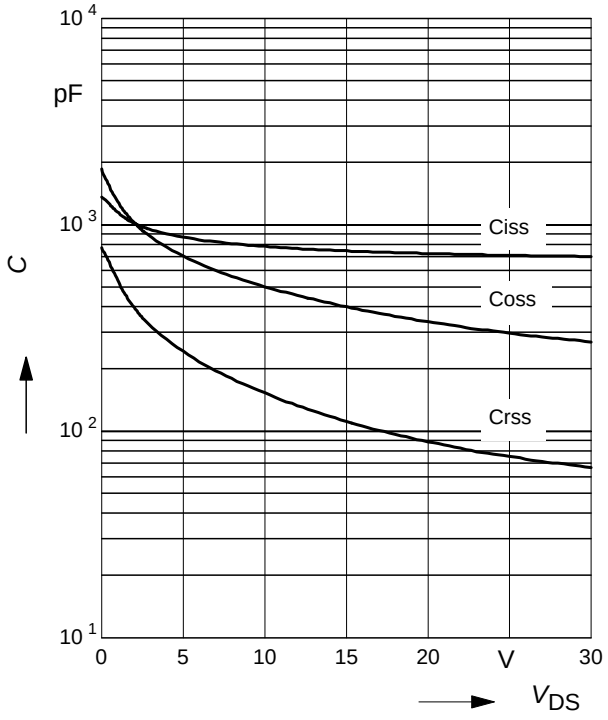
parameter: $V_{GS} = V_{DS}$, I_D = 30 µA



11 Typ. capacitances

$C = f(V_{DS})$

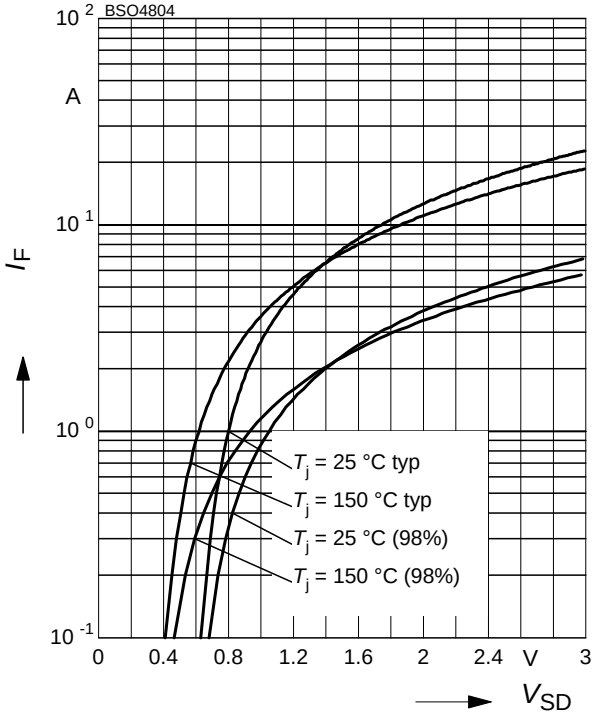
parameter: V_{GS}=0V, f=1 MHz



12 Forward character. of reverse diode

$I_F = f(V_{SD})$

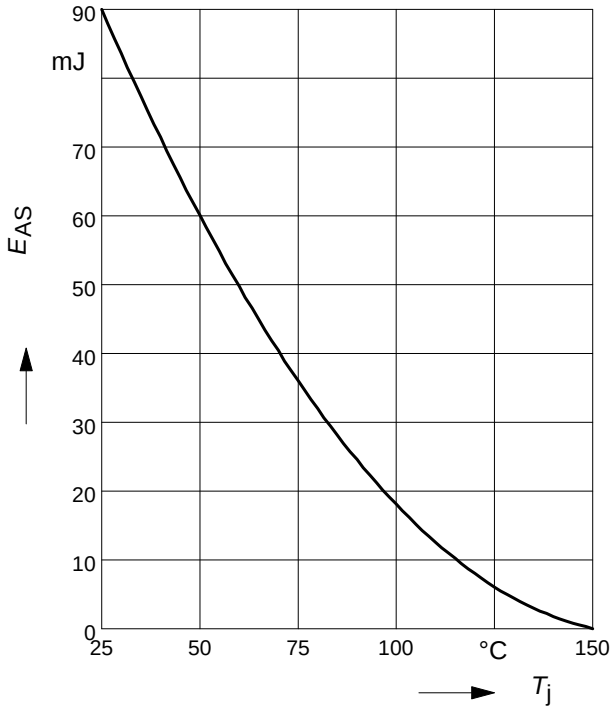
parameter: T_j , tp = 80 µs



13 Typ. avalanche energy

$E_{AS} = f(T_j)$

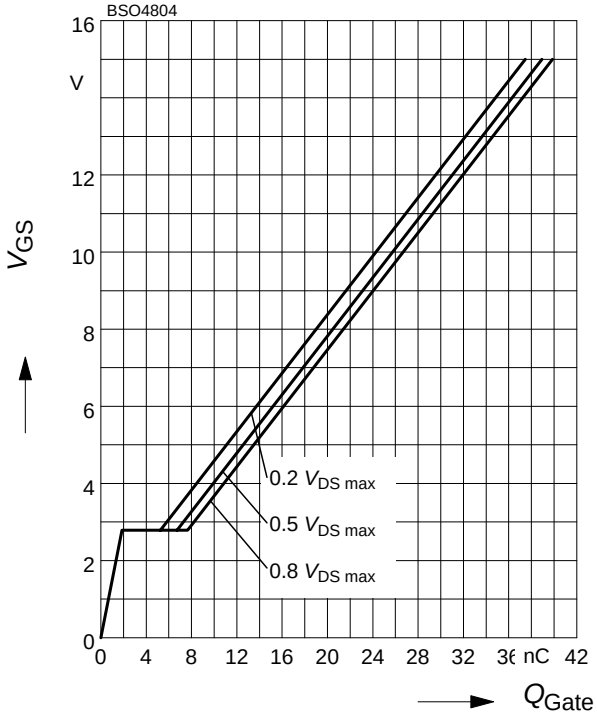
par.: I_D = 8 A , V_{DD} = 25 V, R_{GS} = 25 Ω



14 Typ. gate charge

$V_{GS} = f(Q_{Gate})$

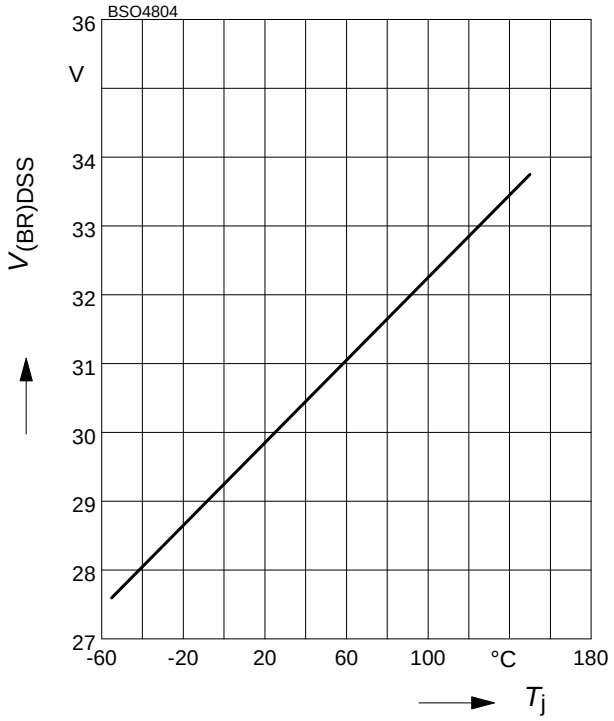
parameter: I_D = 8 A pulsed



15 Drain-source breakdown voltage

$V_{(BR)DSS} = f(T_j)$

parameter: I_D=10 mA



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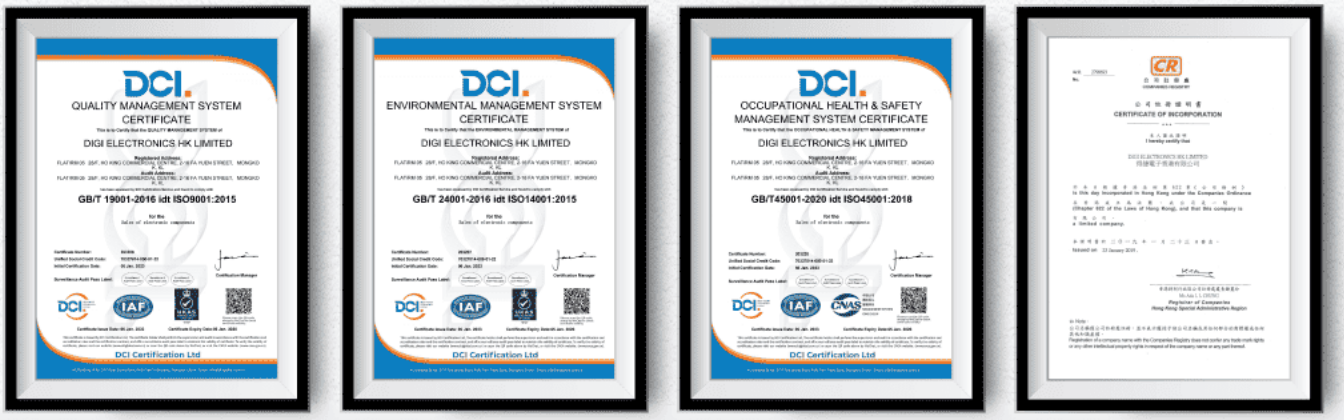

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